

DESCRIPTION

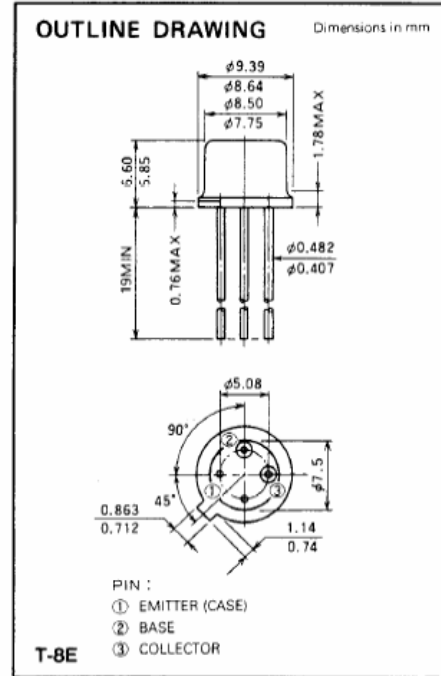
2SC3101 is a silicon NPN epitaxial planar type transistor specifically designed for UHF power amplifiers applications.

FEATURES

- High power gain: $G_{pe} \geq 5.7\text{dB}$
@ $V_{CC} = 12.5\text{V}$, $f = 520\text{MHz}$, $P_{in} = 0.8\text{W}$
- Emitter ballasted construction
- High ruggedness: Ability to withstand more than 20:1 load VSWR when operated at @ $V_{CC} = 15.2\text{V}$, $f = 520\text{MHz}$, $P_O = 3\text{W}$.

APPLICATION

For drive stage and output stage of power amplifiers in UHF band.



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CEO}	Collector to base voltage		35	V
V_{EBO}	Emitter to base voltage		4	V
V_{CEO}	Collector to emitter voltage	$R_{BE} = \infty$	17	V
I_C	Collector current		1	A
P_C	Collector dissipation	$T_C = 25^\circ\text{C}$	10	W
T_J	Junction temperature		175	$^\circ\text{C}$
T_{stg}	Storage temperature		-55 to 175	$^\circ\text{C}$

Note: Above parameters are guaranteed independently.

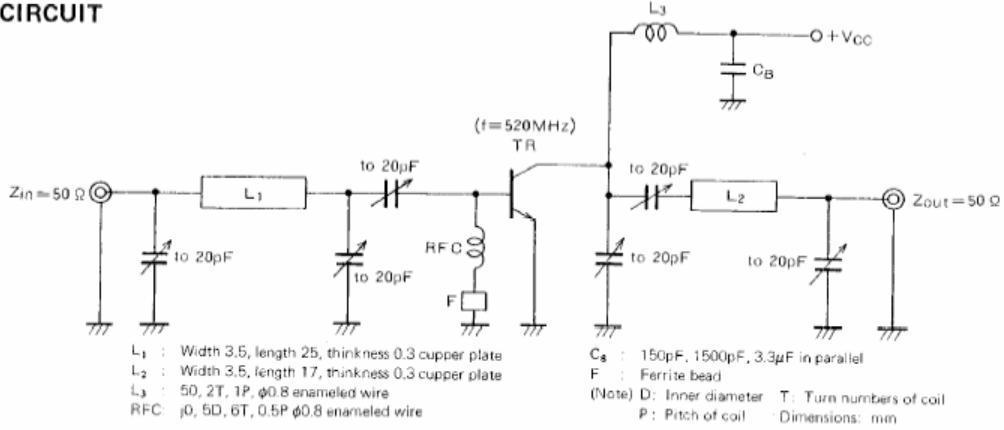
ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)EBO}$	Emitter to base breakdown voltage	$I_E = 1\text{mA}$, $I_C = 0$	4			V
$V_{(BR)CBO}$	Collector to base breakdown voltage	$I_C = 10\text{mA}$, $I_E = 0$	35			V
$V_{(BR)CEO}$	Collector to emitter breakdown voltage	$I_C = 10\text{mA}$, $R_{BE} = \infty$	17			V
I_{CBO}	Collector cutoff current	$V_{CB} = 15\text{V}$, $I_E = 0$			300	μA
I_{EBO}	Emitter cutoff current	$V_{EB} = 2\text{V}$, $I_C = 0$			300	μA
h_{FE}	DC forward current gain *	$V_{CB} = 10\text{V}$, $I_C = 0.1\text{A}$	10	50	180	—
P_O	Output power	$V_{CC} = 12.5\text{V}$, $P_{in} = 0.8\text{W}$, $f = 520\text{MHz}$.	3	3.5		W
η_C	Collector efficiency		50	60		%

Note: * Pulse test, $P_W = 150\mu\text{s}$, duty = 5%.

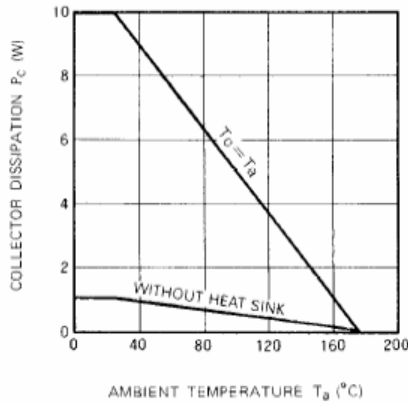
Above parameters, ratings, limits and conditions are subject to change.

TEST CIRCUIT

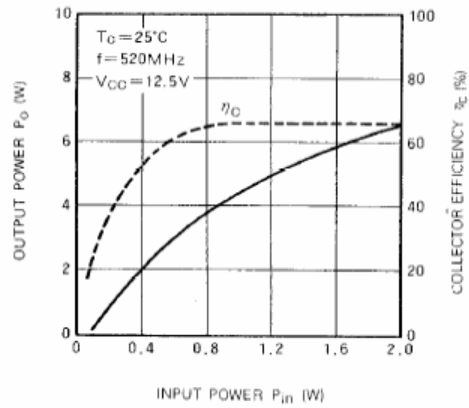


TYPICAL PERFORMANCE DATA

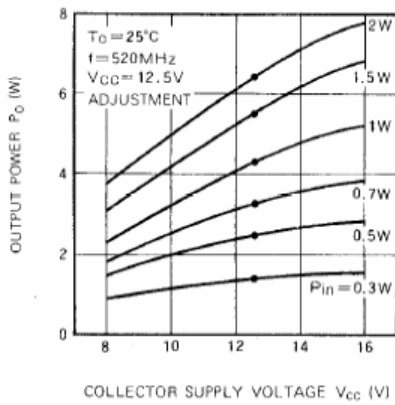
COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE CHARACTERISTICS



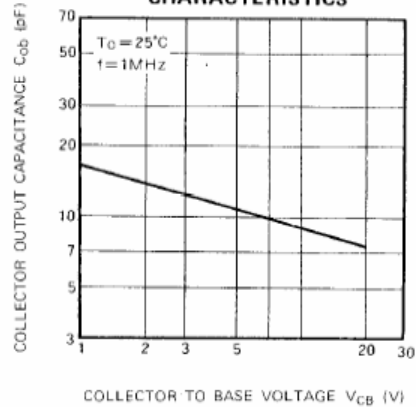
OUTPUT POWER, COLLECTOR EFFICIENCY VS. INPUT POWER CHARACTERISTICS



OUTPUT POWER VS. COLLECTOR SUPPLY VOLTAGE CHARACTERISTICS



COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE CHARACTERISTICS





Sales Offices

<p>CHINA</p> <p>ELEFLOW TECHNOLOGIES(HQ) Suite1-603, HuaKang Plaza 109 ZhenXing Road, Futian District ShenZhen518031, P.R. China Phone: 86-755-83204665/83204663 Fax: 86-755-8320 4659 Email: eleflow@163.com</p> <p>USA</p> <p>ELEFLOW TECHNOLOGIES(USA) Mr. Ted Seymore (Manager) 3291 NE 4th Ave., Boca Raton Florida 33431-6011, USA Phone: 561-302-7007 Fax: 561- 852-0505 Email: tedseymour@adelphia.net</p>	<p>R & D CENTER</p> <p>ELEFLOW TECHNOLOGIES(R&D CENTER) Overseas Chinese High-Tech Venture Park No. 12 South, Hi-tech Park, NanShan Dist. ShenZhen518057, China</p>
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